

Inventor: Kamran ZARRINEH et al.

Title: AUTOMATIC GENERATION AND VALIDATION OF

MEMORY TEST MODELS

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Docket No.: SMQ-072

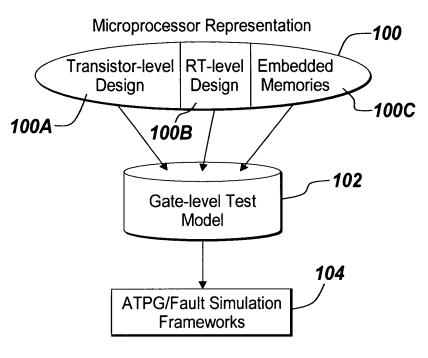


Fig. 1
(Prior Art)

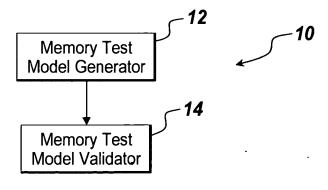


Fig. 2

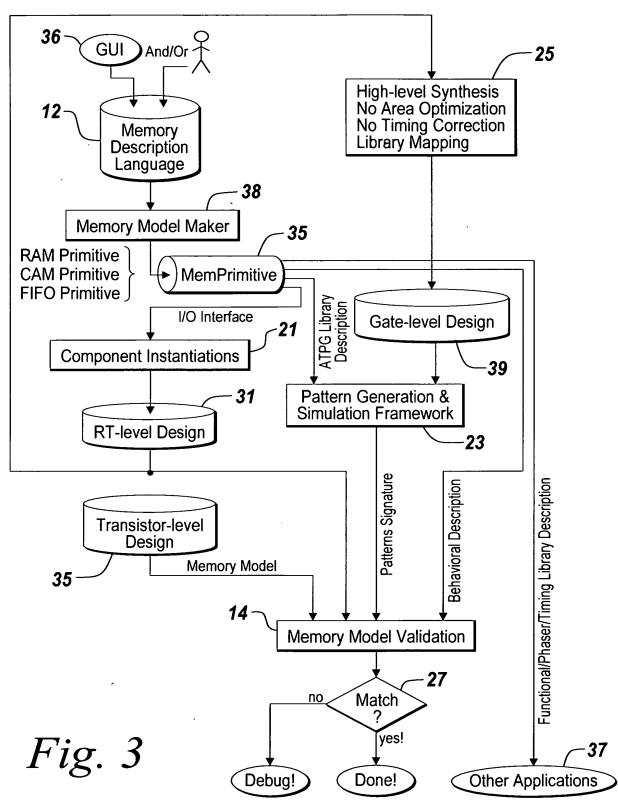
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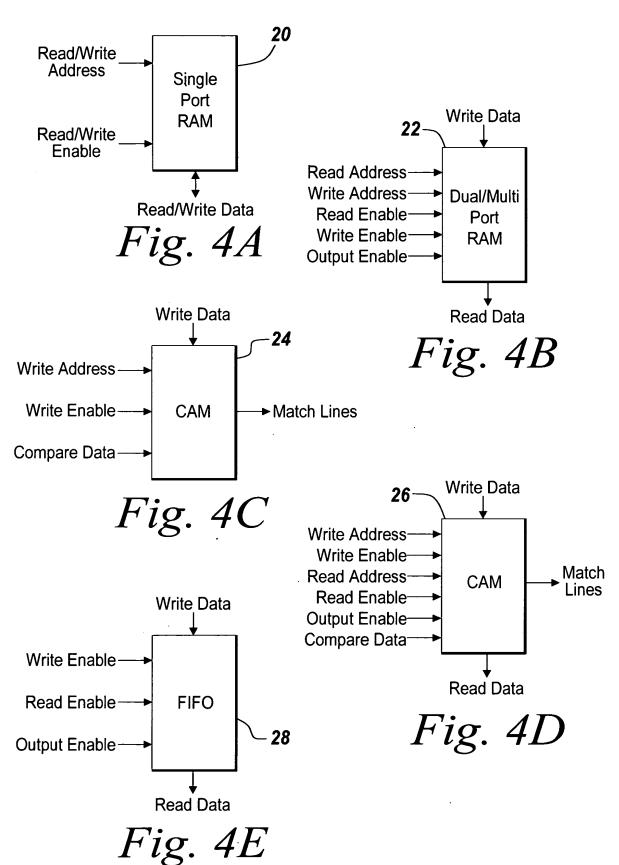
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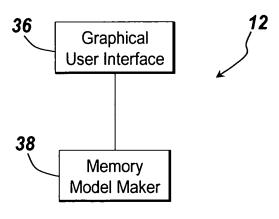


Fig. 5

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module <memory\_name> /\* where <memory name> is the RT-level name of the memory; 2 CLASS = {REGISTER FILE, SRAM, DRAM]; 3 FUNCTION = {RAM, CAM, FIFO}; WIDTH = <integer>; /\* where integer indicates the data width of the memory. 5 DEPTH = <integer>; /\* where integer indicates the address depth of the memory. 6 MIN ADDRESS = <integer>; MAX ADDRESS = <integer>; /\* The minimum and maximum addressable locations for read and write ports. \*/ READ\_ADDRESS = {decoded, encoded}; 8 WRITE ADDRESS = {decoded, encoded}; /\* Fully decoded and encoded address signals. \*/ 10 PORTS = {R=<integer>,W=<integer>,RW=<integer>,C=<integer>,S, R}; /\* Where R: read only ports, W: write only ports, RW: read and write ports, \*/ /\* C: compare ports, S: set port, R: reset port WRITE POLARITIES={W Dpolarity, W Apolarity, W Epolarity, W C L Kpolarity}: 11 /\* polarity = $\{+, -\}$ /\* WD+ | WD- : write data acts as an A | B phase latch /\* WA+ | WA- : write address acts as an A | B phase latch /\* WE+ | WE- : write enable acts as an A | B phase latch /\* WCLK+ | WCLK-: actual write occurs on the rising/falling edge READ POLARITIES={ $RD^{polarity}$ ,  $RA^{polarity}$ ,  $RE^{polarity}$ ,  $RCLK^{polarity}$ }: 12 /\* polarity =  $\{+, -\}$ /\*RD+ | RD- : read data acts as an A | B phase latch /\* RA+ | RA- : read address acts as an A | B phase latch /\* RE+ | RE- : read enable acts as an A | B phase latch /\* RCLK+ | RCLK- : read occurs on the rising/falling edge RR RESOLUTION= $\{R, X\}$ ; 13 /\* where R: indicates that the location could be read 14 WW RESOLUTION={true, false}; /\* where true: indicates that two ports can write to the same location 15 PORT ARBITRATION={port names}; /\* The order the port names appear in the list determines the dominant ports. \*/ RW RESOLUTION={NW, XW, OW, XX, OX}; 16 /\* where NW: reading new data and writing the data /\* XW: reading X and writing the data /\* OW: reading old data and writing data /\* XX: reading and writing Xs /\* OX: reading old data and writing X 17 endmodule;



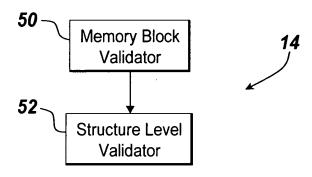
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*Fig.* 7

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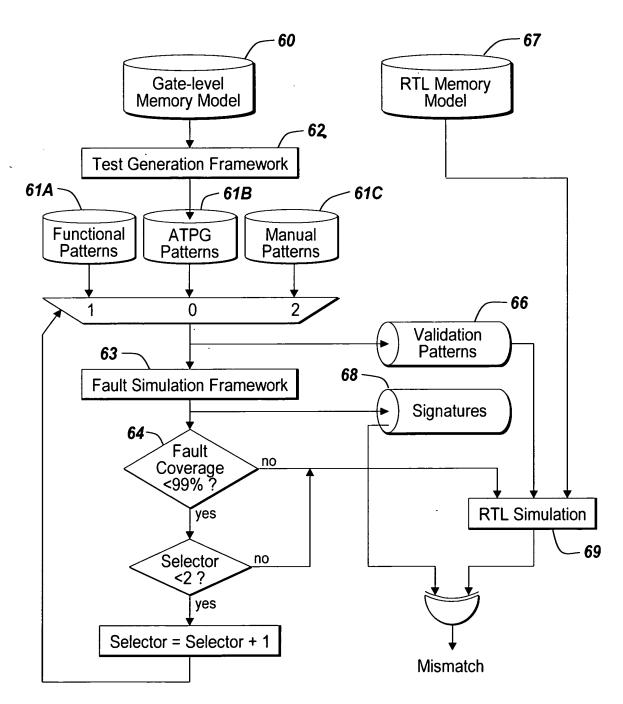


Fig. 8